NSN 5962-01-414-0581

Memory Microcircuit - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5962-01-414-0581

Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Agm-130/tvgs
Features Provided:
Electrostatic sensitive and ultraviolet erasable and monolithic and programmable
Inclosure Material:
Silicon
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Criticality Code Justification:
Cbbl
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit-eraseable programmable read only memory
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 7.0 volts total supply
Time Rating Per Chacteristic:
55.00 nanoseconds af output megawatts
Memory Device Type:
Eprom
Special Features:
Altered item, make from p/n 5962-8953702yx, dwg name microcircuits, memory, digital, cmos, 16k x 8 uv eprom, monolithic silicon;
endurance 25 cycles/byte,
Test Data Document:
96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
28 printed circuit
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
Yes - demil/mli
Fiig:

A458a0